

BGB741L7ESD

ESD-Robust and Easy-To-Use Broadband LNA
MMIC

RF & Protection Devices



Edition 2009-04-17

**Published by Infineon Technologies AG,
85579 Neubiberg, Germany**

**© Infineon Technologies AG 2009.
All Rights Reserved.**

Attention please!

The information herein is given to describe certain components and shall not be considered as a guarantee of characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

BGB741L7ESD, ESD-Robust and Easy-To-Use Broadband LNA MMIC

Revision History: 2009-04-17, Rev. 1.0

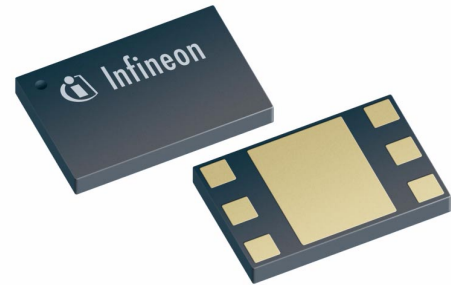
Prevision History: no previous version

Page	Subjects (major changes since last revision)

1 ESD-Robust and Easy-To-Use Broadband LNA MMIC

Features

- High-performance broadband LNA MMIC for applications between 50 MHz and 5.5 GHz
- Integrated stabilization, biasing, matching and ESD-protection simplifies design and reduces external parts count
- Integrated active biasing circuit makes operation point highly stable against temperature- and processing-variations
- Integrated ESD protection: RF input pin typical 4 kV vs. GND, RF output pin 2.5 kV vs. GND (HBM stress pulses)
- Supply voltage 1.8 - 4.0 V
- Adjustable current 6 mA to 30 mA by an external resistor
- Power-off function
- Excellent noise figure for a broadband LNA by using latest SiGe:C bipolar technology
- High linearity due to active biasing
- Very small, leadless, Pb-free (RoHS compliant) and halogen-free (WEEE compliant) "green" package TSLP-7-1, 2.0 x 1.3 x 0.4 mm



RoHS



Applications

- Mobile TV, DAB, RKE, AMR, Cellular, ZigBee, WiMAX, SDARs, WiFi, Cordless phone, UMTS, WLAN, UWB

2 Product Brief

The BGB741L7ESD is an advanced high performance low noise amplifier (LNA) MMIC which simplifies the design of arbitrary LNA application circuits. Due to its integrated feedback the device is perfectly matched up to 3.5 GHz. The integrated biasing further reduces external parts count and stabilizes the bias current against temperature- and process-variations. The integrated feedback provides unconditional stability and eases the design process. The device is highly flexible because the bias current is adjustable and the device works with a broad supply voltage range. The BGB741L7ESD is based upon Infineon Technologies' cost effective bipolar silicon germanium carbon (SiGe:C) technology and comes in a low profile TSLP-7-1 leadless "green" package.

Type	Package	Marking
BGB741L7ESD	TSLP-7-1	AY

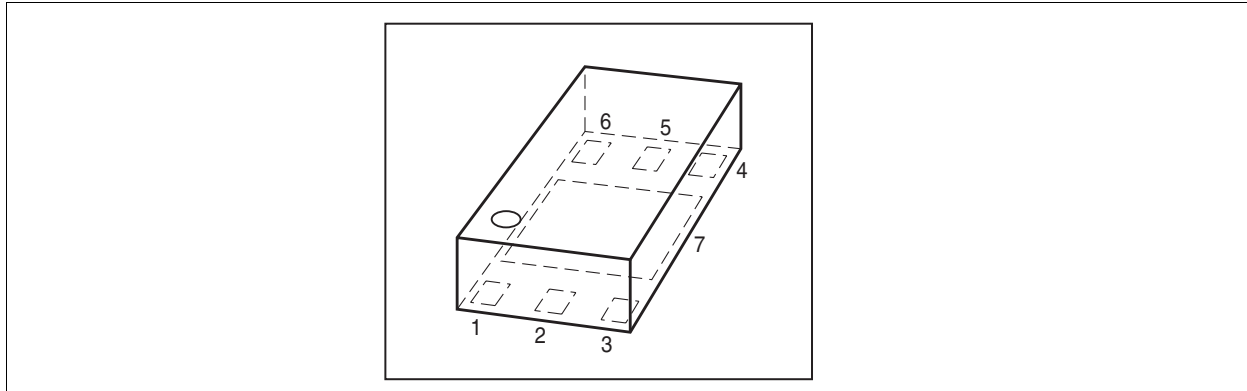


Figure 1 Pin configuration

Table 1 Pinning table

Pin	Function
1	V_{CC}
2	Bias-Out
3	RF-In
4	RF-Out
5	Control On/Off
6	Current Adjust
7	GND

The following diagram shows the principal schematic how the BGB741L7ESD is used in a circuit. The Power On/Off function is used by applying V_{ctrl} . By applying an external resistor R_{ext} the pre-set current of 6mA (which is adjusted by the integrated biasing when R_{ext} is omitted) can be increased. Base- and collector voltages are applied to the respective RFin- and RFout-pins by external inductors.

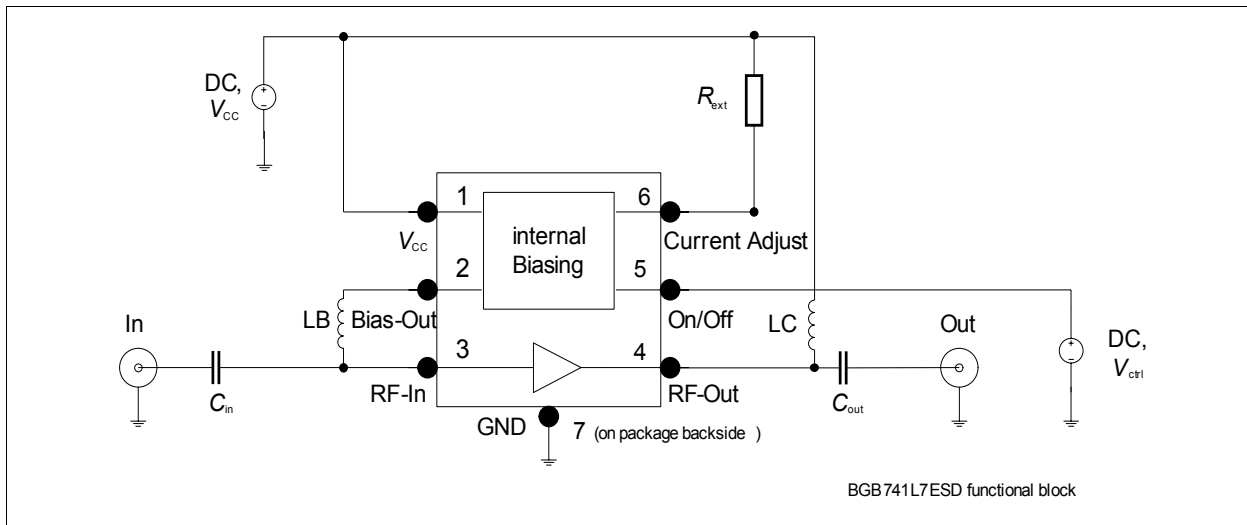


Figure 2 Functional block diagram

3 Maximum Ratings

Table 2 Maximum ratings at $T_A = 25^\circ\text{C}$ (unless otherwise specified)

Parameter	Symbol	Value	Unit
Supply voltage $T_A = -55^\circ\text{C}$	V_{CC}	4.0 3.5	V
Supply current at V_{CC} pin	I_{CC}	30	mA
DC current at RF In pin	I_B	3	mA
Voltage at Control On / Off pin	V_{ctrl}	4.0	V
Total power dissipation ¹⁾ $T_S < 117^\circ\text{C}$	P_{tot}	120	mW
Operation junction temperature	T_{JOp}	-55...150	$^\circ\text{C}$
Storage temperature	T_{Stg}	-55...150	$^\circ\text{C}$

1) The soldering point temperature T_S measured at the GND pin (7) at the soldering point to the pcb

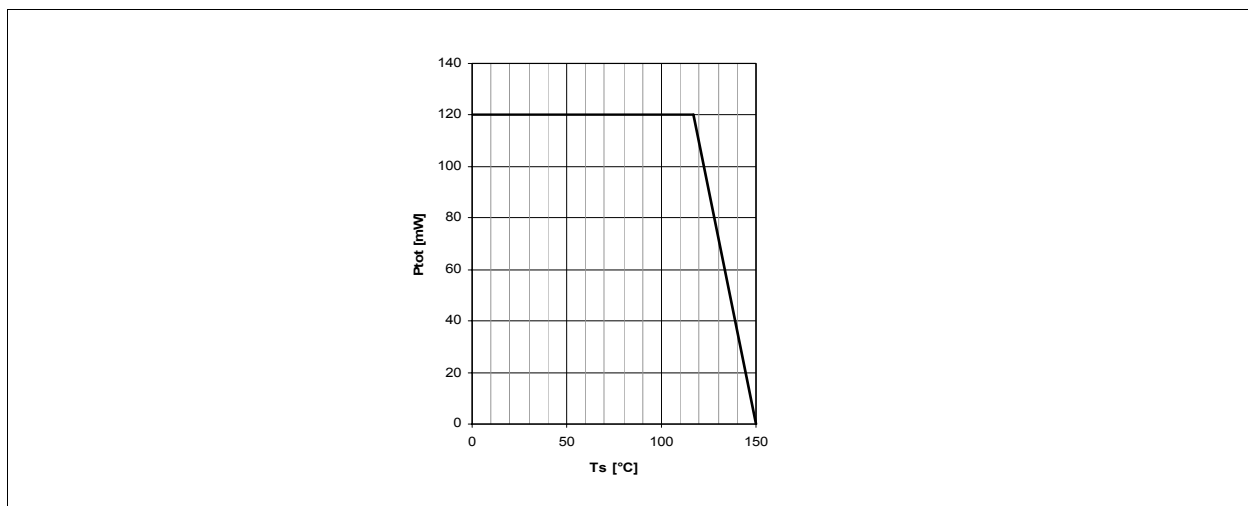
Note: Exceeding only one of the above maximum rating limits even for a short moment may cause permanent damage to the device. Even if the device continues to operate, its lifetime may be considerably shortened. Maximum ratings are stress ratings only and do not mean unaffected functional operation and lifetime at others than standard operation conditions.

4 Thermal Characteristics

Table 3 Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	275	K/W

1) For calculation of R_{thJA} please refer to Application Note Thermal Resistance


Figure 3 Maximum total Power Dissipation P_{tot} as function of temperature T_S at soldering point

5 Operation Conditions

Table 4 Operation Conditions

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply voltage	V_{CC}	1.8	3.0	4.0	V	
Voltage Control On/Off pin in On mode	$V_{ctrl-on}$	1.2		4.0	V	
Voltage Control On/Off pin in Off mode	$V_{ctrl-off}$	-0.3		0.3	V	

6 Electrical Characteristics

6.1 DC Characteristics

Table 5 DC characteristics at $T_A = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply current in On-mode	I_{CC}	5.0	6.0 10	7.2	mA	$R_{ext} = \text{open}$ $R_{ext} = 4\text{ k}\Omega$ $V_{CC} = 3.0\text{ V}$ $V_{ctrl} = 3.0\text{ V}$ (Small signal operation)
Supply current in Off mode	I_{CC-off}			6.0	μA	$V_{CC} = 3.0\text{ V}$ $V_{ctrl} = 0\text{ V}$
Current into Control On/Off pin in On-mode	$I_{ctrl-on}$		14	20	μA	$V_{CC} = 3.0\text{ V}$ $V_{ctrl} = 3.0\text{ V}$
Current into Control On/Off pin in Off-mode	$I_{ctrl-off}$			0.1	μA	$V_{CC} = 3.0\text{ V}$ $V_{ctrl} = 0\text{ V}$

6.2 AC Characteristics

The measurement setup is a test fixture with Bias-T's in a 50 Ω system, $T_A = 25\text{ °C}$.

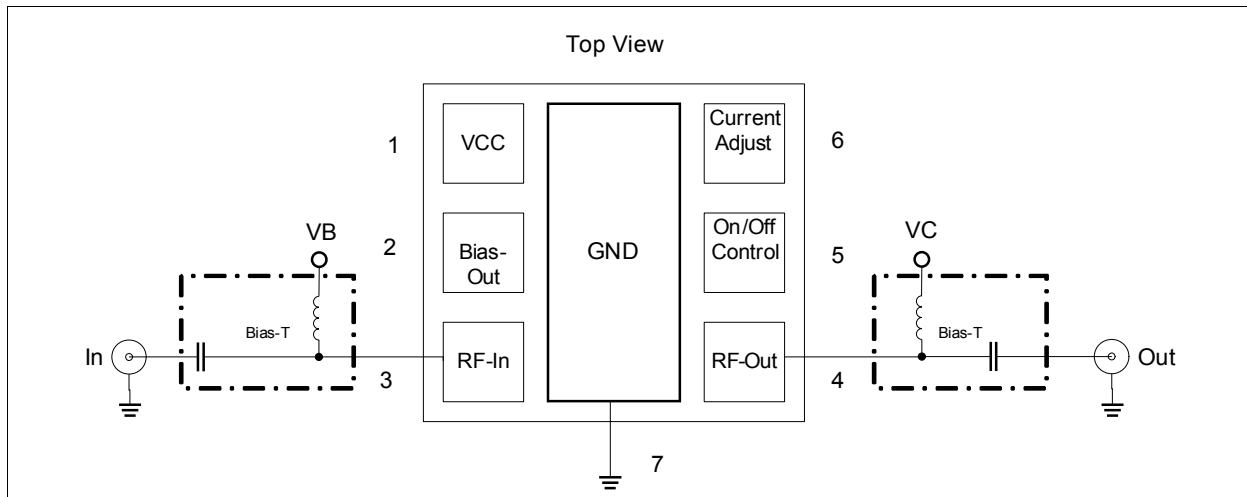


Figure 4 BGB741L7ESD testing setup

Table 6 AC Characteristics, $V_C = 3\text{ V}$, $f = 150\text{ MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Minimum Noise Figure ¹⁾	NF_{\min}		1.05 0.95		dB	$Z_S = Z_{\text{Sopt}}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Noise Figure in 50Ω System ²⁾	NF_{50}		1.1 1.05		dB	$Z_S = Z_L = 50\Omega$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Transducer Gain	$ S_{21} ^2$		19 21		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Maximum Stable Power Gain	G_{ms}		20 21.5		dB	$Z_L = Z_{\text{Lopt}}, Z_S = Z_{\text{Sopt}}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Input 1 dB Gain compression point ³⁾	$IP_{1\text{dB}}$		-5.5 -8		dBm	$I_{\text{Cq}} = 6\text{ mA}$ $I_{\text{Cq}} = 10\text{ mA}$
Input 3 rd Order Intercept Point	IIP_3		5.5 3.5		dBm	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Input Return Loss	$R.L._{\text{in}}$		14 18		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Output Return Loss	$R.L._{\text{out}}$		12.5 18.5		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$

1) Test fixture losses extracted

2) Test fixture losses extracted

3) Measured on an application board according to figure 2) presenting roughly a 50 Ω system to the device. I_{Cq} is the quiescent current, that is at small RF input power level. I_C increases as RF input power level approaches P1dB.

Table 7 AC Characteristics, $V_C = 3\text{ V}$, $f = 450\text{ MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Minimum Noise Figure ¹⁾	NF_{\min}		1.05 0.95		dB	$Z_S = Z_{\text{Sopt}}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Noise Figure in 50Ω System ²⁾	NF_{50}		1.1 1.05		dB	$Z_S = Z_L = 50\Omega$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Transducer Gain	$ S_{21} ^2$		18.5 20.5		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Maximum Available Power Gain	G_{ma}		19 20.5		dB	$Z_L = Z_{\text{Lopt}}$, $Z_S = Z_{\text{Sopt}}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Input 1 dB Gain compression point ³⁾	$IP_{1\text{dB}}$		-5 -7.5		dBm	$I_{\text{Cq}} = 6\text{ mA}$ $I_{\text{Cq}} = 10\text{ mA}$
Input 3 rd Order Intercept Point	IIP_3		4 2.5		dBm	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Input Return Loss	$R.L._{\text{in}}$		15.5 21		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Output Return Loss	$R.L._{\text{out}}$		14.5 28		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$

1) Test fixture losses extracted

2) Test fixture losses extracted

3) Measured on an application board according to figure 2) presenting roughly a 50 Ω system to the device. I_{Cq} is the quiescent current, that is at small RF input power level. I_C increases as RF input power level approaches P1dB.

Table 8 AC Characteristics, $V_C = 3\text{ V}$, $f = 900\text{ MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Minimum Noise Figure ¹⁾	NF_{\min}		1.05 0.95		dB	$Z_S = Z_{\text{Sopt}}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Noise Figure in 50Ω System ²⁾	NF_{50}		1.1 1.05		dB	$Z_S = Z_L = 50\Omega$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Transducer Gain	$ S_{21} ^2$		18.5 20		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Maximum Available Power Gain	G_{ma}		19 20.5		dB	$Z_L = Z_{\text{Lopt}}$, $Z_S = Z_{\text{Sopt}}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Input 1 dB Gain compression point ³⁾	$IP_{1\text{dB}}$		-5 -7		dBm	$I_{\text{Cq}} = 6\text{ mA}$ $I_{\text{Cq}} = 10\text{ mA}$
Input 3 rd Order Intercept Point	IIP_3		3 1.5		dBm	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$

Electrical Characteristics
Table 8 AC Characteristics, $V_C = 3\text{ V}$, (cont'd) $f = 900\text{ MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input Return Loss	$R.L._{in}$		15.5 19		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Output Return Loss	$R.L._{out}$		14.5 28.5		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$

- 1) Test fixture losses extracted
- 2) Test fixture losses extracted
- 3) Measured on an application board according to figure 2) presenting roughly a $50\ \Omega$ system to the device. I_{Cq} is the quiescent current, that is at small RF input power level. I_C increases as RF input power level approaches P1dB.

Table 9 AC Characteristics, $V_C = 3\text{ V}$, $f = 1500\text{ MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Minimum Noise Figure ¹⁾	NF_{min}		1.05 1.0		dB	$Z_S = Z_{Sopt}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Noise Figure in $50\ \Omega$ System ²⁾	NF_{50}		1.1 1.05		dB	$Z_S = Z_L = 50\ \Omega$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Transducer Gain	$ S_{21} ^2$		18 19.5		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Maximum Available Power Gain	G_{ma}		18.5 20		dB	$Z_L = Z_{Lopt}$, $Z_S = Z_{Sopt}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Input 1 dB Gain compression point	IP_{1dB}		-4.5 -6.5		dBm	$I_{Cq} = 6\text{ mA}$ $I_{Cq} = 10\text{ mA}$
Input 3 rd Order Intercept Point ³⁾	IIP_3		2.5 1		dBm	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Input Return Loss	$R.L._{in}$		14.5 16		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Output Return Loss	$R.L._{out}$		14 23		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$

- 1) Test fixture losses extracted
- 2) Test fixture losses extracted
- 3) Measured on an application board according to figure 2) presenting roughly a $50\ \Omega$ system to the device. I_{Cq} is the quiescent current, that is at small RF input power level. I_C increases as RF input power level approaches P1dB.

Table 10 AC Characteristics, $V_C = 3\text{ V}$, $f = 1900\text{ MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Minimum Noise Figure ¹⁾	NF_{\min}		1.05 1.05		dB	$Z_S = Z_{\text{Sopt}}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Noise Figure in 50Ω System ²⁾	NF_{50}		1.15 1.1		dB	$Z_S = Z_L = 50\Omega$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Transducer Gain	$ S_{21} ^2$		17.5 19		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Maximum Available Power Gain	G_{ma}		18 19.5		dB	$Z_L = Z_{\text{Lopt}}, Z_S = Z_{\text{Sopt}}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Input 1 dB Gain compression point	$IP_{1\text{dB}}$		-4 -6		dBm	$I_{\text{Cq}} = 6\text{ mA}$ $I_{\text{Cq}} = 10\text{ mA}$
Input 3 rd Order Intercept Point ³⁾	IIP_3		2.5 1		dBm	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Input Return Loss	$R.L._{\text{in}}$		13.5 15		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Output Return Loss	$R.L._{\text{out}}$		13.5 21		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$

1) Test fixture losses extracted

2) Test fixture losses extracted

3) Measured on an application board according to figure 2) presenting roughly a 50 Ω system to the device. I_{Cq} is the quiescent current, that is at small RF input power level. I_C increases as RF input power level approaches P1dB.

Table 11 AC Characteristics, $V_C = 3\text{ V}$, $f = 2400\text{ MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Minimum Noise Figure ¹⁾	NF_{\min}		1.1 1.05		dB	$Z_S = Z_{\text{Sopt}}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Noise Figure in 50Ω System ²⁾	NF_{50}		1.15 1.1		dB	$Z_S = Z_L = 50\Omega$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Transducer Gain	$ S_{21} ^2$		17 18.5		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Maximum Available Power Gain	G_{ma}		17.5 19		dB	$Z_L = Z_{\text{Lopt}}, Z_S = Z_{\text{Sopt}}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Input 1 dB Gain compression point ³⁾	$IP_{1\text{dB}}$		-3.5 -5.5		dBm	$I_{\text{Cq}} = 6\text{ mA}$ $I_{\text{Cq}} = 10\text{ mA}$
Input 3 rd Order Intercept Point	IIP_3		3 1		dBm	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$

Electrical Characteristics
Table 11 AC Characteristics, $V_C = 3\text{ V}$, (cont'd) $f = 2400\text{ MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input Return Loss	$R.L._{in}$		12.5 13.5		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Output Return Loss	$R.L._{out}$		12.5 18		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$

- 1) Test fixture losses extracted
- 2) Test fixture losses extracted
- 3) Measured on an application board according to figure 2) presenting roughly a $50\ \Omega$ system to the device. I_{Cq} is the quiescent current, that is at small RF input power level. I_C increases as RF input power level approaches P1dB.

Table 12 AC Characteristics, $V_C = 3\text{ V}$, $f = 3500\text{ MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Minimum Noise Figure ¹⁾	NF_{min}		1.25 1.2		dB	$Z_S = Z_{Sopt}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Noise Figure in $50\ \Omega$ System ²⁾	NF_{50}		1.35 1.25		dB	$Z_S = Z_L = 50\ \Omega$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Transducer Gain	$ S_{21} ^2$		15 16.5		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Maximum Available Power Gain	G_{ma}		16 17.5		dB	$Z_L = Z_{Lopt}$, $Z_S = Z_{Sopt}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Input 1 dB Gain compression point ³⁾	IP_{1dB}		-2.5 -4.5		dBm	$I_{Cq} = 6\text{ mA}$ $I_{Cq} = 10\text{ mA}$
Input 3 rd Order Intercept Point	IIP_3		3.5 1.5		dBm	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Input Return Loss	$R.L._{in}$		10 10.5		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Output Return Loss	$R.L._{out}$		10 13.5		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$

- 1) Test fixture losses extracted
- 2) Test fixture losses extracted
- 3) Measured on an application board according to figure 2) presenting roughly a $50\ \Omega$ system to the device. I_{Cq} is the quiescent current, that is at small RF input power level. I_C increases as RF input power level approaches P1dB.

Table 13 AC Characteristics, $V_C = 3\text{ V}$, $f = 5500\text{ MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Minimum Noise Figure ¹⁾	NF_{\min}		1.8 1.75		dB	$Z_S = Z_{\text{Sopt}}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Noise Figure in 50Ω System ²⁾	NF_{50}		1.95 1.85		dB	$Z_S = Z_L = 50\Omega$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Transducer Gain	$ S_{21} ^2$		12 13		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Maximum Available Power Gain	G_{ma}		14 15		dB	$Z_L = Z_{\text{Lopt}}$, $Z_S = Z_{\text{Sopt}}$ $I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Input 1 dB Gain compression point ³⁾	$IP_{1\text{dB}}$		-1 -3		dBm	$I_{\text{Cq}} = 6\text{ mA}$ $I_{\text{Cq}} = 10\text{ mA}$
Input 3 rd Order Intercept Point	IIP_3		8.5 4		dBm	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Input Return Loss	$R.L._{\text{in}}$		7 8		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$
Output Return Loss	$R.L._{\text{out}}$		7 8.5		dB	$I_C = 6\text{ mA}$ $I_C = 10\text{ mA}$

1) Test fixture losses extracted

2) Test fixture losses extracted

3) Measured on an application board according to figure 2) presenting roughly a 50 Ω system to the device. I_{Cq} is the quiescent current, that is at small RF input power level. I_C increases as RF input power level approaches P1dB.

7 Package Information

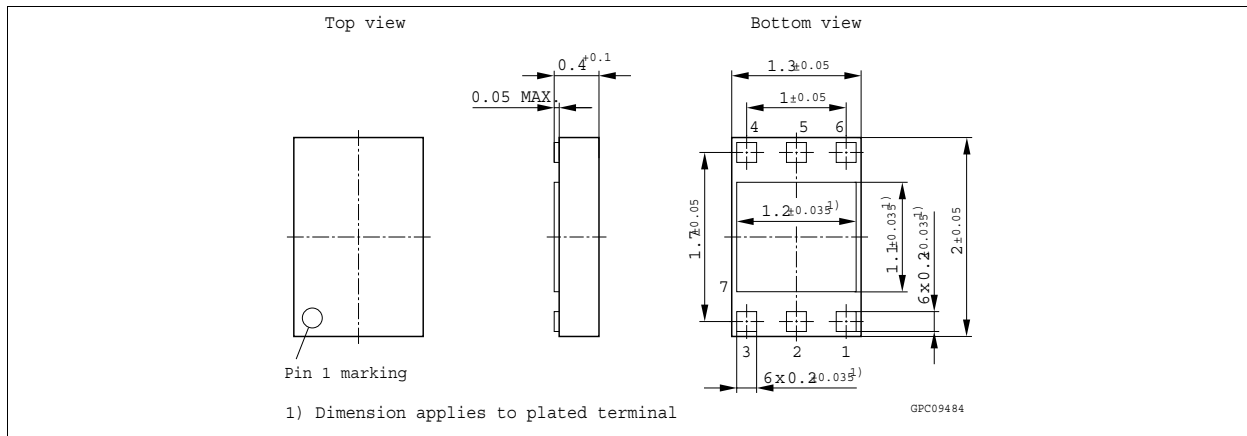


Figure 5 Package Outline of TSLP-7-1

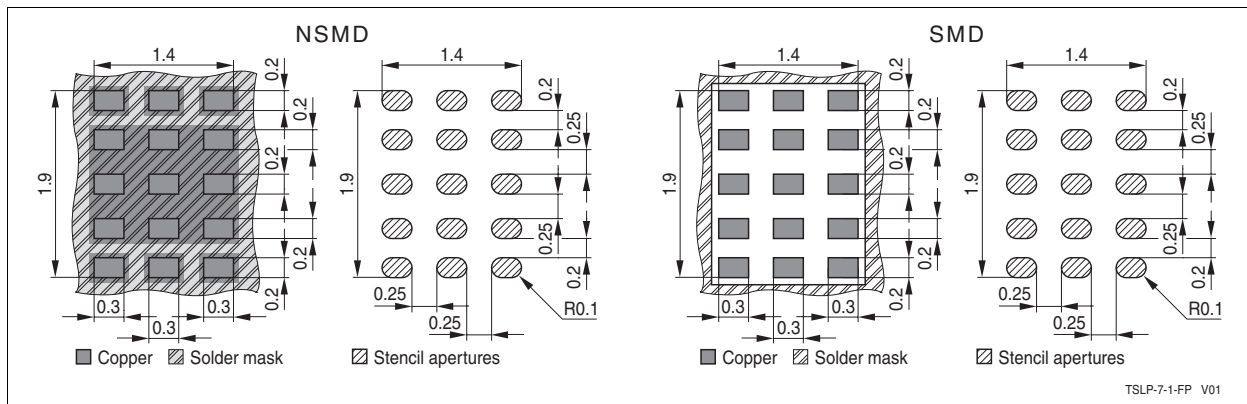


Figure 6 Foot Print of TSLP-7-1

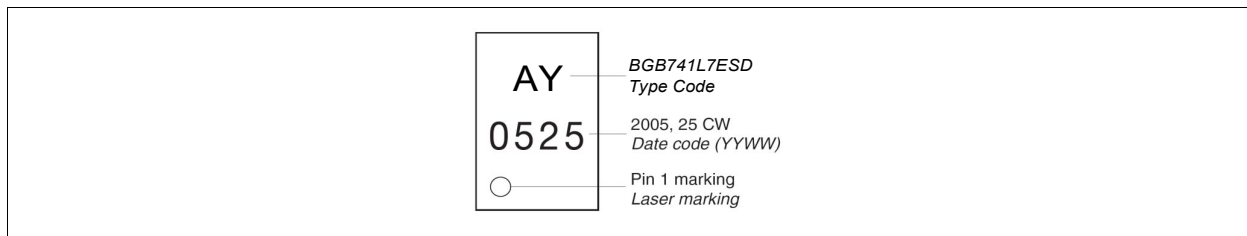


Figure 7 Marking Layout of TSLP-7-1

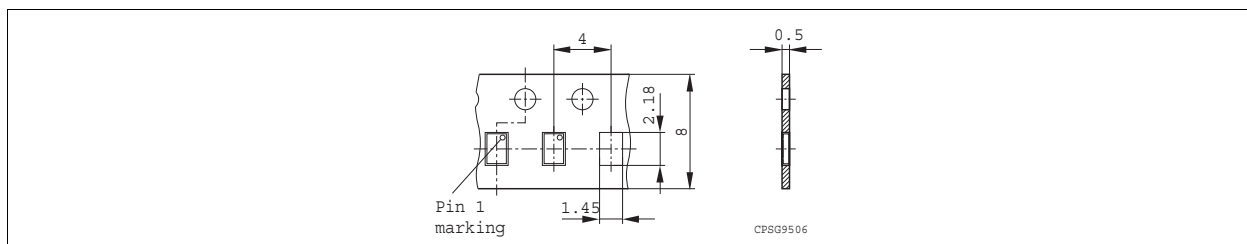


Figure 8 Tape of TSLP-7-1